

# LM48580 Boomer™ Audio Power Amplifier Series High Efficiency Class H, High Voltage, Haptic Piezo Actuator / Ceramic Speaker Driver

## 1 Features

- Class H Driver
- Integrated Boost Converter
- Bridge-tied Load Output
- Differential Input
- Three Pin-Programmable Gains
- Low Supply Current
- Minimum External components
- Micro-Power Shutdown
- Thermal Overload Protection
- Available in Space-Saving 12-bump DSBGA Package

## 2 Applications

- Touch Screen Smart Phones
- Tablet PCs
- Portable Electronic Devices
- MP3 Players
- Key Specifications:
  - Output Voltage at  $V_{DD} = 3.6\text{ V}$ ,  $R_L = 6\ \mu\text{F} + 10\ \Omega$ ,  $\text{THD+N} \leq 1\%$
  - $30\text{ V}_{P-P}$  (Typical)
  - Quiescent Power Supply Current at  $3.6\text{ V}$ 
    - $2.7\text{ mA}$  (Typical)
  - Power Dissipation at  $25\text{ V}_{P-P}$ 
    - $800\text{ mW}$  (Typical)
  - Shutdown Current
    - $0.1\ \mu\text{A}$  (Typical)

## 3 Description

The LM48580 is a fully differential, high voltage driver for piezo actuators and ceramic speakers for portable multi-media devices. Part of TI's Powerwise™ product line, the LM48580 Class H architecture offers significant power savings compared to traditional Class AB amplifiers. The device provides  $30\text{ V}_{P-P}$  output drive while consuming just  $15\text{ mW}$  of quiescent power.

The LM48580 is a single supply driver with an integrated boost converter which allows the device to deliver  $30\text{ V}_{P-P}$  from a single  $3.6\text{ V}$  supply.

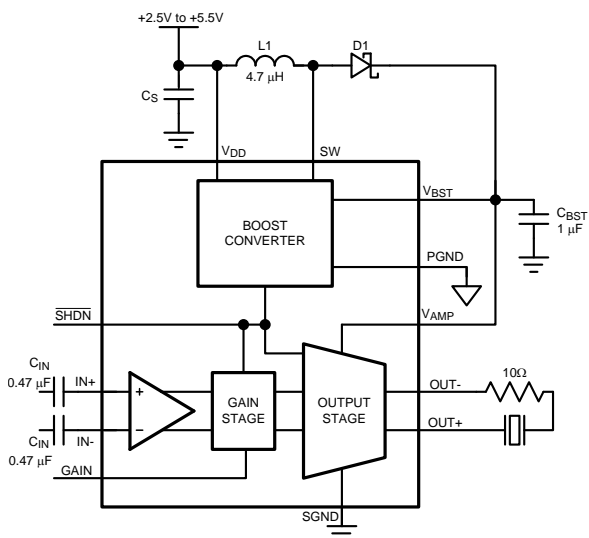
The LM48580 has three pin-programmable gain settings and a low power Shutdown mode that reduces quiescent current consumption to  $0.1\ \mu\text{A}$ . The LM48580 is available in an ultra-small 12-bump DSBGA package.

### Device Information<sup>(1)</sup>

| PART NUMBER | PACKAGE | BODY SIZE (NOM)   |
|-------------|---------|-------------------|
| LM48580     | DSBGA   | 2.00 mm x 1.80 mm |

(1) For all available packages, see the orderable addendum at the end of the data sheet.

### Typical Application



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## 4 Revision History

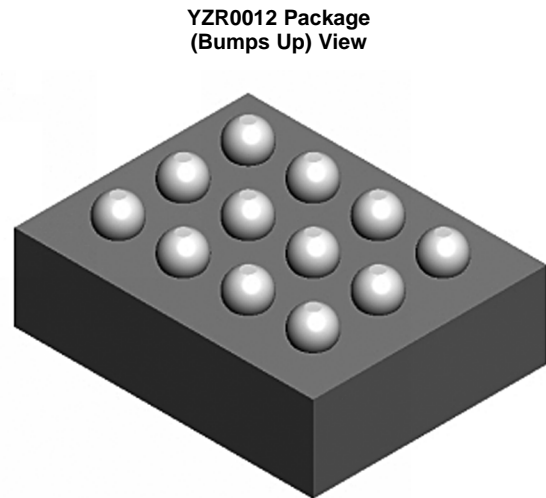
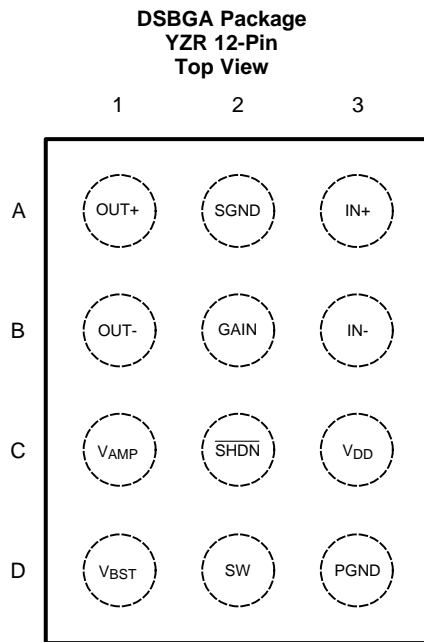
NOTE: Page numbers for previous revisions may differ from page numbers in the current version.

| <b>Changes from Revision A (May 2013) to Revision B</b>  | <b>Page</b> |
|--|-------------|
| • Added <i>Device Information</i> table, <i>ESD</i> table, <i>Thermal Information</i> table, <i>Parameter Measurement Information</i> , <i>Feature Description</i> , <i>Device Functional Modes</i> , <i>Power Supply Recommendations</i> , <i>Layout</i> section, <i>Device and Documentation Support</i> , and <i>Mechanical, Packaging, and Orderable Information</i> ..... | <b>1</b>    |
| • Deleted the <i>Demoboard Bill of Materials</i> section .....   | <b>12</b>   |
| • Deleted the <i>Demo Board Schematic</i> section.....   | <b>12</b>   |

| <b>Changes from Original (February 2010) to Revision A</b> | <b>Page</b> |
|--|-------------|
| • Changed layout of National Data Sheet to TI format. .... | <b>1</b>    |

## 5 Pin Configuration and Functions



### Pin Functions

| Bump | Name                     | Description  |
|------|--------------------------|--|
| A1   | OUT+                     | Amplifier Non-Inverting Output   |
| A2   | SGND                     | Amplifier Ground   |
| A3   | IN+                      | Amplifier Non-Inverting Input  |
| B1   | OUT-                     | Amplifier Inverting Output   |
| B2   | GAIN                     | Gain Select:<br>GAIN = float: A <sub>V</sub> = 18dB<br>GAIN = GND: A <sub>V</sub> = 24dB<br>GAIN = V <sub>DD</sub> : A <sub>V</sub> = 30dB           |
| B3   | IN-                      | Amplifier Inverting Input  |
| C1   | V <sub>AMP</sub>         | Amplifier Supply Voltage. Connect to V <sub>BST</sub>  |
| C2   | $\overline{\text{SHDN}}$ | Active Low Shutdown. Drive $\overline{\text{SHDN}}$ low to disable device. Connect $\overline{\text{SHDN}}$ to V <sub>DD</sub> for normal operation. |
| C3   | V <sub>DD</sub>          | Power Supply   |
| D1   | V <sub>BST</sub>         | Boost Converter Output   |
| D2   | SW                       | Boost Converter Switching Node   |
| D3   | PGND                     | Boost Converter Ground   |

## 6 Specifications

## 7 Absolute Maximum Ratings

 over operating free-air temperature range (unless otherwise noted)<sup>(1)(2)</sup>

|                                       | MIN  | MAX                   | UNIT |
|---------------------------------------|------|-----------------------|------|
| Supply Voltage                        |      | 6                     | V    |
| SW Voltage                            |      | 25                    | V    |
| VBST Voltage                          |      | 21                    | V    |
| V <sub>AMP</sub>                      |      | 17                    | V    |
| Input Voltage                         | -0.3 | V <sub>DD</sub> + 0.3 | V    |
| Storage temperature, T <sub>stg</sub> | -65  | 150                   | °C   |
| Junction Temperature                  |      | 150                   | °C   |

- Stresses beyond those listed under *Absolute Maximum Ratings* may cause permanent damage to the device. These are stress ratings only, which do not imply functional operation of the device at these or any other conditions beyond those indicated under *Recommended Operating Conditions*. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.
- If Military/Aerospace specified devices are required, please contact the Texas Instruments Sales Office/Distributors for availability and specifications.

## 8 ESD Ratings

|  |  | VALUE | UNIT |
|--|--|-------|------|
| V <sub>(ESD)</sub> Electrostatic discharge | Human-body model (HBM), per ANSI/ESDA/JEDEC JS-001 <sup>(1)</sup>              | ±2000 | V    |
|  | Charged-device model (CDM), per JEDEC specification JESD22-C101 <sup>(2)</sup> | ±750  |      |

- JEDEC document JEP155 states that 500-V HBM allows safe manufacturing with a standard ESD control process.
- JEDEC document JEP157 states that 250-V CDM allows safe manufacturing with a standard ESD control process.

## 9 Recommended Operating Conditions

over operating free-air temperature range (unless otherwise noted)

|                   | MIN | NOM             | MAX | UNIT |
|-------------------|-----|-----------------|-----|------|
| Temperature Range | -40 | T <sub>A</sub>  | 85  | °C   |
| Supply Voltage    | 2.5 | V <sub>DD</sub> | 5.5 | V    |

## 10 Thermal Information

| THERMAL METRIC <sup>(1)</sup> |  | LM48580     | UNIT |
|-------------------------------|--|-------------|------|
|                               |  | YZR (DSBGA) |      |
|                               |  | 12 PINS     |      |
| R <sub>θJA</sub>              | Junction-to-ambient thermal resistance       | 82.1        | °C/W |
| R <sub>θJC(top)</sub>         | Junction-to-case (top) thermal resistance    | 0.6         | °C/W |
| R <sub>θJB</sub>              | Junction-to-board thermal resistance         | 20.6        | °C/W |
| ψ <sub>JT</sub>               | Junction-to-top characterization parameter   | 0.4         | °C/W |
| ψ <sub>JB</sub>               | Junction-to-board characterization parameter | 20.7        | °C/W |
| R <sub>θJC(bot)</sub>         | Junction-to-case (bottom) thermal resistance | n/a         | °C/W |

- For more information about traditional and new thermal metrics, see the [Semiconductor and IC Package Thermal Metrics](#) application report.

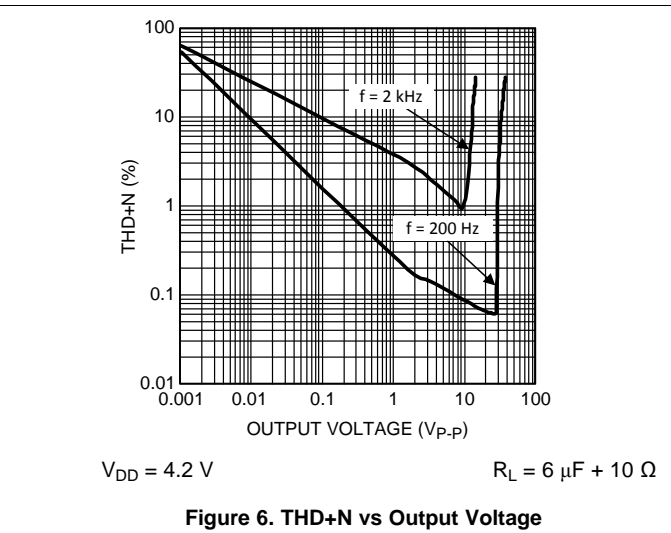
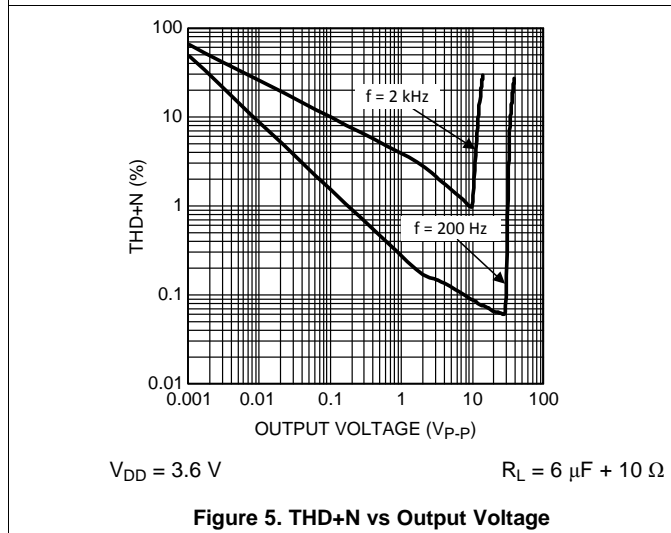
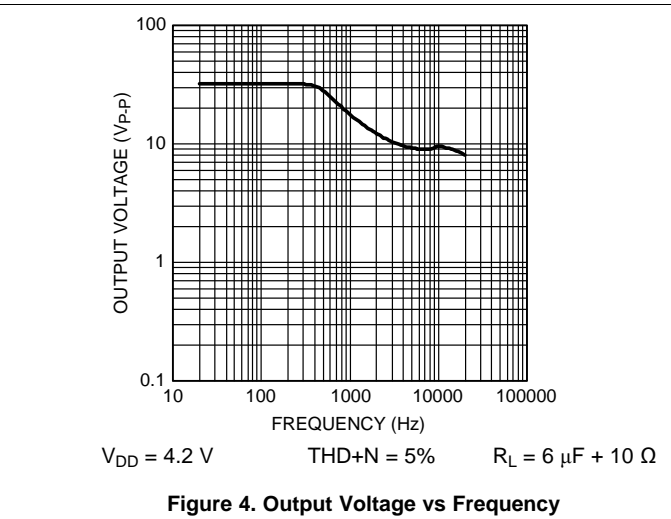
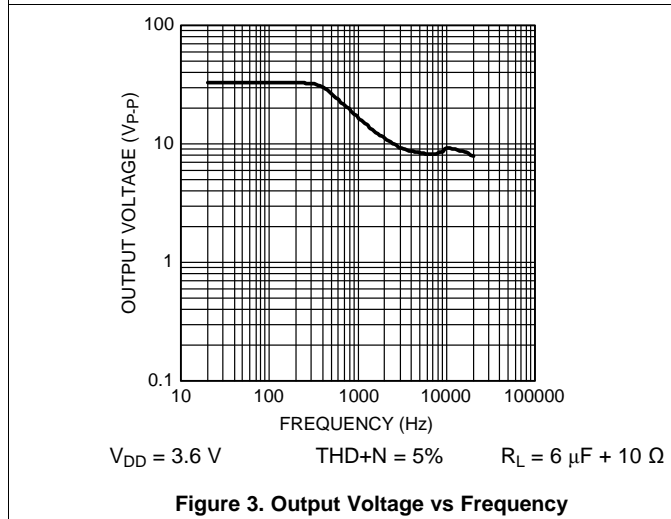
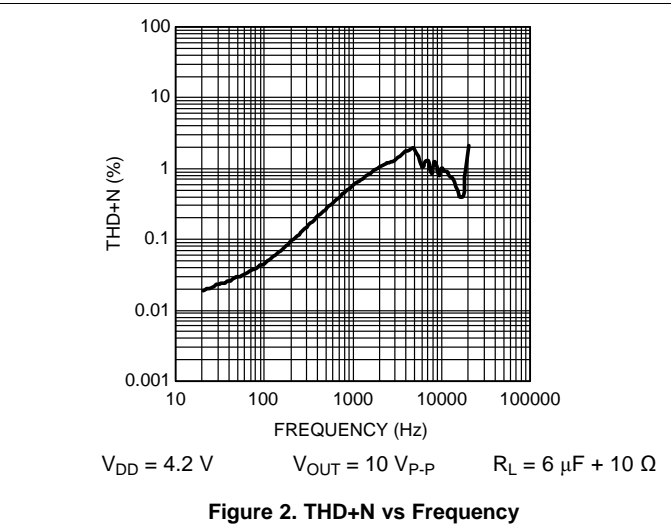
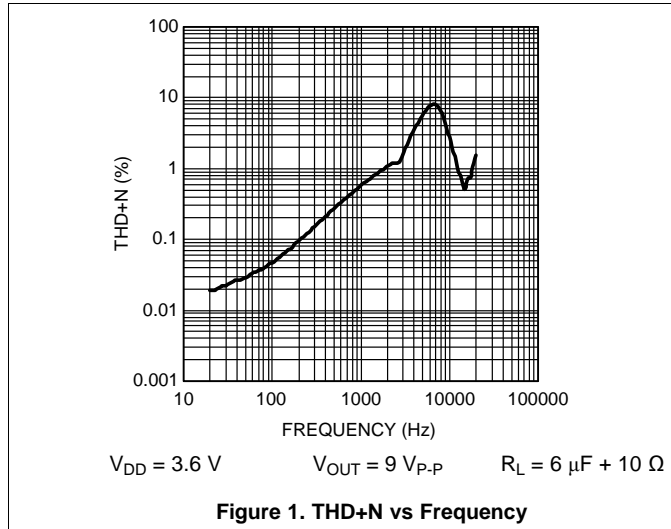
## 11 Electrical Characteristics: $V_{DD} = 3.6\text{ V}^{(1)}$

The following specifications apply for  $R_L = 6\ \mu\text{F} + 10\ \Omega$ ,  $C_{BST} = 1\ \mu\text{F}$ ,  $C_{IN} = 0.47\ \mu\text{F}$ ,  $A_V = 24\ \text{dB}$  unless otherwise specified. Limits apply for  $T_A = 25^\circ\text{C}$ .

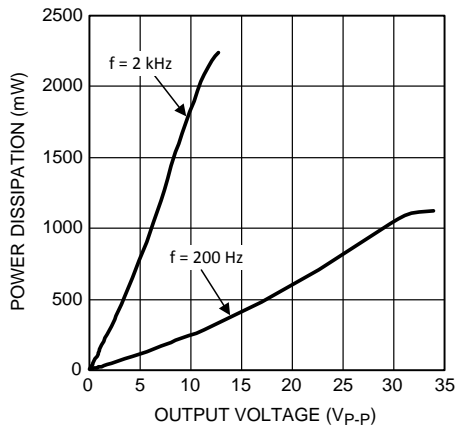
| PARAMETER   |  | TEST CONDITIONS                            | Min <sup>(2)</sup> | Typ <sup>(3)</sup> | Max <sup>(2)</sup> | Unit          |
|-------------|--|--|--------------------|--------------------|--------------------|---------------|
| $V_{DD}$    | Supply Voltage Range   |  | 2.5                |                    | 5.5                | V             |
| $I_{DD}$    | Quiescent Power Supply Current,<br>$V_{IN} = 0\text{V}$ , $R_L = \infty$                               | $V_{DD} = 3.6\text{V}$                     |                    | 2.7                | 4                  | mA            |
|             |  | $V_{DD} = 3\text{V}$                       |                    | 3                  |                    | mA            |
| $P_D$       | Power Consumption<br>$V_{OUT} = 25_{P-P}$ , $f = 200\ \text{Hz}$                                       | $V_{DD} = 3.6\text{V}$                     |                    | 800                |                    | mW            |
|             |  | $V_{DD} = 3\text{V}$                       |                    | 830                |                    | mW            |
| $I_{SD}$    | Shutdown Current   | Shutdown Enabled                           |                    | 0.5                | 2                  | $\mu\text{A}$ |
| $T_{WU}$    | Wake-up Time   | From Shutdown                              | 1                  | 1.4                | 1.6                | ms            |
| $V_{OS}$    | Differential Output Offset Voltage   | $V_{DD} = 3.6\ \text{V}$                   |                    | 63                 | 360                | mV            |
| $A_V$       | Gain   | GAIN = FLOAT                               | 17.5               | 18                 | 18.5               | dB            |
|             |  | GAIN = GND                                 | 23.5               | 24                 | 24.5               | dB            |
|             |  | GAIN = $V_{DD}$                            | 29.5               | 30                 | 30.5               | dB            |
| $R_{IN}$    | Input Resistance   |  | 46                 | 52                 | 58                 | k $\Omega$    |
| $R_{IN}$    | Gain Input Resistance  | to GND                                     |                    |                    | 575                | k $\Omega$    |
|             |  | to $V_{DD}$                                |                    |                    | 131                | k $\Omega$    |
| $V_{IN}$    | Maximum Input Voltage Range  | $A_V = 18\text{dB}$                        |                    |                    | 3                  | $V_{P-P}$     |
| $V_{OUT}$   | Output Voltage<br>$f = 200\ \text{Hz}$ , THD+N = 1%  | $V_{DD} = 3.6\ \text{V}$                   | 25                 | 30.5               |                    | $V_{P-P}$     |
|             |  | $V_{DD} = 3\ \text{V}$                     |                    | 30.5               |                    | $V_{P-P}$     |
|             | Output Voltage<br>$f = 2\ \text{kHz}$ , THD+N = 5%   | $V_{DD} = 3.6\ \text{V}$                   |                    | 11                 |                    | $V_{P-P}$     |
|             |  | $V_{DD} = 3\ \text{V}$                     |                    | 8.5                |                    | $V_{P-P}$     |
| THD+N       | Total Harmonic Distortion + Noise  | $V_{OUT} = 25V_{P-P}$ , $f = 200\text{Hz}$ |                    | 0.16%              |                    |               |
| PSRR        | Power Supply Rejection Ratio<br>$V_{DD} = 3.6\ \text{V} + 200\ \text{mV}_{P-P}$ sine,<br>Inputs AC GND | $f_{RIPPLE} = 217\ \text{Hz}$ ,            |                    | 75                 |                    | dB            |
|             |  | $f_{RIPPLE} = 1\ \text{kHz}$               |                    | 71                 |                    | dB            |
| CMRR        | Common Mode Rejection Ratio<br>$V_{CM} = 200\text{mV}_{P-P}$ sine                                      | $f_{RIPPLE} = 217\ \text{Hz}$              |                    | 56                 |                    | dB            |
|             |  | $f_{RIPPLE} = 1\ \text{kHz}$               |                    | 55                 |                    | dB            |
| $f_{SW}$    | Boost Converter Switching Frequency  |  |                    | 2.1                |                    | MHz           |
| $I_{LIMIT}$ | Boost Converter Current Limit  |  |                    |                    | 1100               | mA            |
| $V_{IH}$    | Logic High Input Threshold   | $\overline{\text{SHDN}}$                   | 1.2                |                    |                    | V             |
| $V_{IL}$    | Logic Low Input Threshold  | $\overline{\text{SHDN}}$                   |                    |                    | 0.45               | V             |
| $I_{IN}$    | Input Leakage Current  | $\overline{\text{SHDN}}$                   |                    | 0.1                | 1                  | $\mu\text{A}$ |

- (1) The *Electrical Characteristics* tables list ensured specifications under the listed *Recommended Operating Conditions* except as otherwise modified or specified by the *Electrical Characteristics Conditions* and/or Notes. Typical specifications are estimations only and are not ensured.
- (2) Datasheet min/max specification limits are specified by design, test, or statistical analysis.
- (3) Typical values represent most likely parametric norms at  $T_A = +25^\circ\text{C}$ , and at the *Recommended Operation Conditions* at the time of product characterization and are not specified.

### 11.1 Typical Performance Characteristics

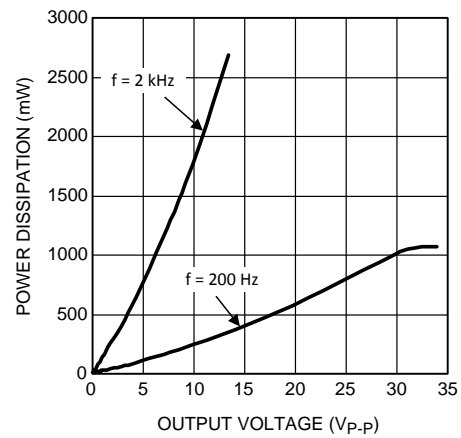


Typical Performance Characteristics (continued)



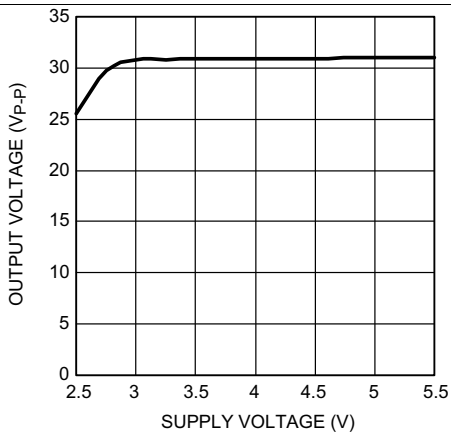
$V_{DD} = 3.6\text{ V}$   $R_L = 6\ \mu\text{F} + 10\ \Omega$

Figure 7. Power Consumption vs Output Voltage



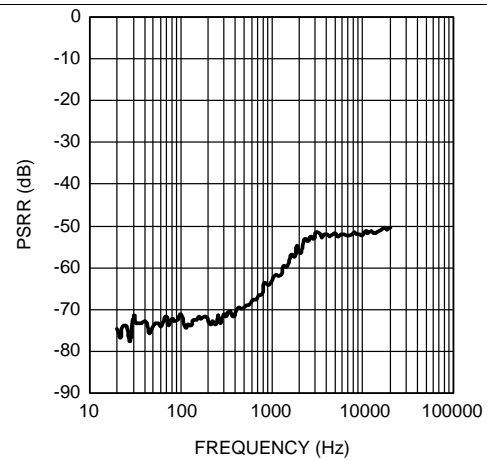
$V_{DD} = 4.2\text{ V}$   $R_L = 6\ \mu\text{F} + 10\ \Omega$

Figure 8. Power Consumption vs Output Voltage



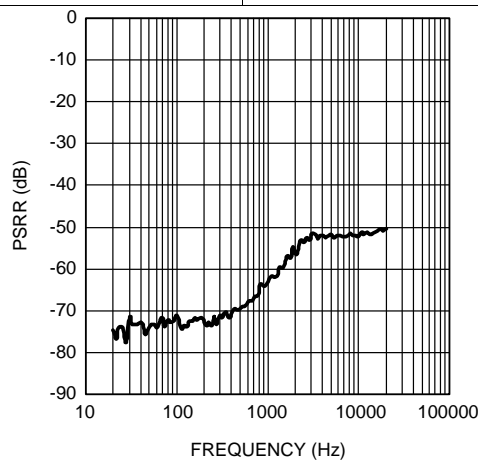
$R_L = 6\ \mu\text{F} + 10\ \Omega$ ,  $f = 200\text{ Hz}$

Figure 9. Output Voltage vs Supply Voltage



$V_{DD} = 3.6\text{ V}$   $f = 200\text{ Hz}$   $R_L = 6\ \mu\text{F} + 10\ \Omega$ ,  
 $V_{RIPPLE} = 200\text{ mV}_{P-P}$

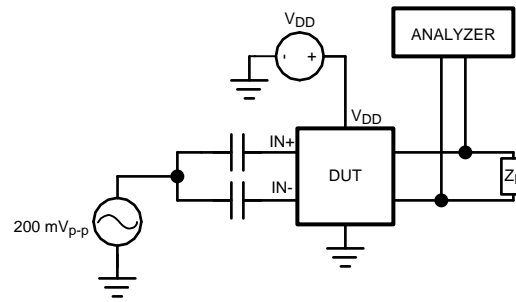
Figure 10. PSRR vs Frequency



$V_{DD} = 3.6\text{ V}$   $V_{CM} = 1\text{ V}_{P-P}$   $R_L = 6\ \mu\text{F} + 10\ \Omega$

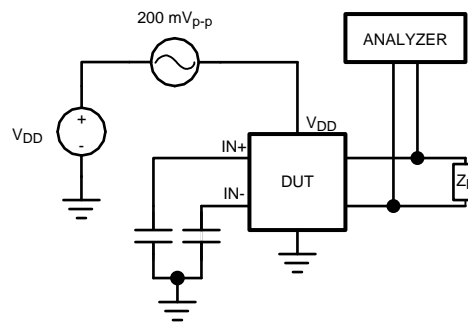
Figure 11. CMRR vs Frequency

## 12 Parameter Measurement Information



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**Figure 12. PSRR Test Circuit**



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**Figure 13. CMRR Test Circuit**

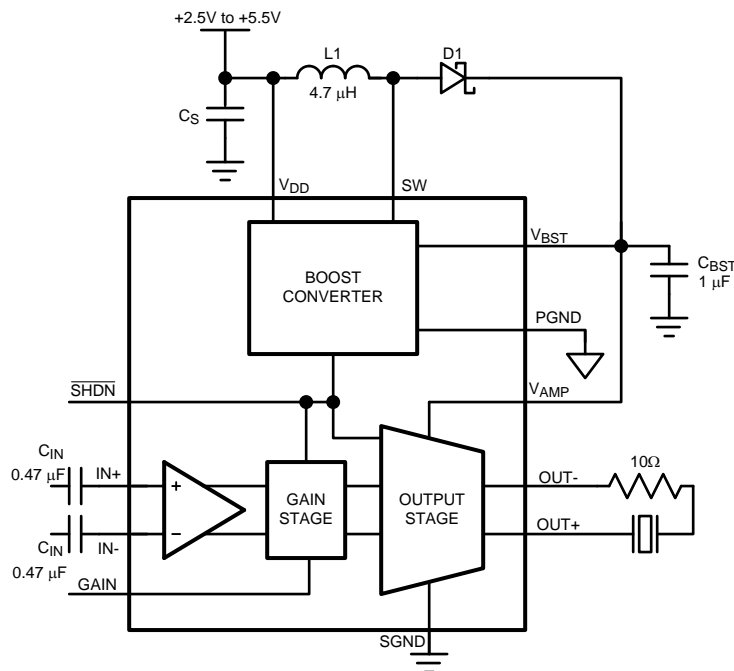


## 13 Detailed Description

### 13.1 Overview

The LM48580 is a fully differential, Class H ceramic element driver for ceramic speakers and haptic actuators. The integrated, high efficiency boost converter dynamically adjusts the amplifier's supply voltage based on the output signal, increasing headroom and improving efficiency compared to a conventional Class AB driver. The fully differential amplifier takes advantage of the increased headroom and bridge-tied load (BTL) architecture, delivering significantly more voltage than a single-ended amplifier.

### 13.2 Functional Block Diagram



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### 13.3 Feature Description

#### 13.3.1 Class H Operation

Class H is a modification of another amplifier class (typically Class B or Class AB) to increase efficiency and reduce power dissipation. To decrease power dissipation, Class H uses a tracking power supply that monitors the output signal and adjusts the supply accordingly. When the amplifier output is below  $3 V_{P-P}$ , the nominal boost voltage is 6 V. As the amplifier output increases above  $3 V_{P-P}$ , the boost voltage tracks the amplifier output as shown in Figure 14. When the amplifier output falls below  $3 V_{P-P}$ , the boost converter returns to its nominal output voltage. Power dissipation is greatly reduced compared to conventional Class AB drivers.

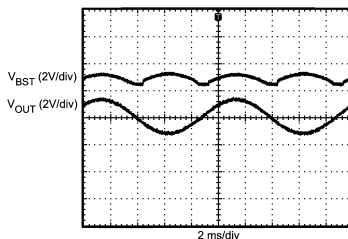


Figure 14. Class H Operation

## Feature Description (continued)

### 13.3.2 Properties of Piezoelectric Elements

Piezoelectric elements such as ceramic speakers or piezoelectric haptic actuators are capacitive in nature. Due to their capacitive nature, piezoelectric elements appear as low impedance loads at high frequencies (typically above 5 kHz). A resistor in series with the piezoelectric element is required to ensure the amplifier does not see a short at high frequencies.

The value of the series resistor depends on the capacitance of the element, the frequency content of the output signal, and the desired frequency response. Higher valued resistors minimize power dissipation at high frequencies, but also impacts the frequency response. This configuration is suited for use with haptic actuators, where the majority of the signal content is typically below 2 kHz. Conversely, lower valued resistors maximize frequency response, while increasing power dissipation at high frequency. This configuration is ideal for ceramic speaker applications, where high frequency audio content needs to be reproduced. Resistor values are typically between 10  $\Omega$  and 20  $\Omega$ .

### 13.3.3 Differential Amplifier Explanation

The LM48580 features a fully differential amplifier. A differential amplifier amplifies the difference between the two input signals. A major benefit of the fully differential amplifier is the improved common mode rejection ratio (CMRR) over single ended input amplifiers. The increased CMRR of the differential amplifier reduces sensitivity to ground offset related noise injection, especially important in noisy systems.

### 13.3.4 Thermal Shutdown

The LM48580 features thermal shutdown that protects the device during thermal overload conditions. When the junction temperature exceeds +160°C, the device is disabled. The LM48580 remains disabled until the die temperature falls below the +160°C and SHDN is toggled.

### 13.3.5 Gain Setting

The LM48580 features three internally configured gain settings 18, 24, and 30 dB. The device gain is selected through a single pin (GAIN). The gain settings are shown in [Table 1](#).

**Table 1. Gain Setting**

| Gain  | Gain Setting |
|-------|--------------|
| FLOAT | 18 dB        |
| GND   | 24 dB        |
| VDD   | 30 dB        |

## 13.4 Device Functional Modes

### 13.4.1 Shutdown Function

The LM48580 features a low current shutdown mode. Set  $\overline{\text{SD}} = \text{GND}$  to disable the amplifier and boost converter and reduce supply current to 0.01 $\mu\text{A}$ .

## 14 Application and Implementation

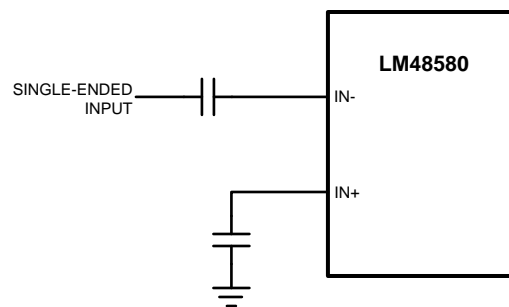
### NOTE

Information in the following applications sections is not part of the TI component specification, and TI does not warrant its accuracy or completeness. TI's customers are responsible for determining suitability of components for their purposes. Customers should validate and test their design implementation to confirm system functionality.

### 14.1 Application Information

### 14.2 Typical Application

The LM48580 is compatible with single-ended sources. When configured for single-ended inputs, input capacitors must be used to block and DC component at the input of the device. [Figure 15](#) shows the typical single-ended applications circuit.



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**Figure 15. Single-Ended Configuration**

#### 14.2.1 Design Requirements

##### 14.2.1.1 Proper Selection of External Components

###### 14.2.1.1.1 Boost Converter Capacitor Selection

The LM48580 boost converter requires three external capacitors for proper operation: a 1  $\mu$ F supply bypass capacitor, and 1  $\mu$ F + 100 pF output reservoir capacitors. Place the supply bypass capacitor as close to  $V_{DD}$  as possible. Place the reservoir capacitors as close to  $V_{BST}$  and  $V_{AMP}$  as possible. Low ESR surface-mount multi-layer ceramic capacitors with X7R or X5R temperature characteristics are recommended. Select output capacitors with voltage rating of 25 V or higher. Tantalum, OS-CON and aluminum electrolytic capacitors are not recommended. See [Table 2](#) for suggested capacitor manufacturers.

## Typical Application (continued)

### 14.2.2 Detailed Design Procedure

#### 14.2.2.1 Boost Converter Output Capacitor Selection

##### 14.2.2.1.1 Inductor Selection

The LM48580 boost converter is designed for use with a 4.7  $\mu\text{H}$  inductor. Table 2 lists various inductors and their manufacturers. Choose an inductor with a saturation current rating greater than the maximum operating peak current of the LM48580 ( $> 1 \text{ A}$ ). This ensures that the inductor does not saturate, preventing excess efficiency loss, over heating and possible damage to the inductor. Additionally, choose an inductor with the lowest possible DCR (series resistance) to further minimize efficiency losses.

**Table 2. Recommended Inductors<sup>(1)</sup>**

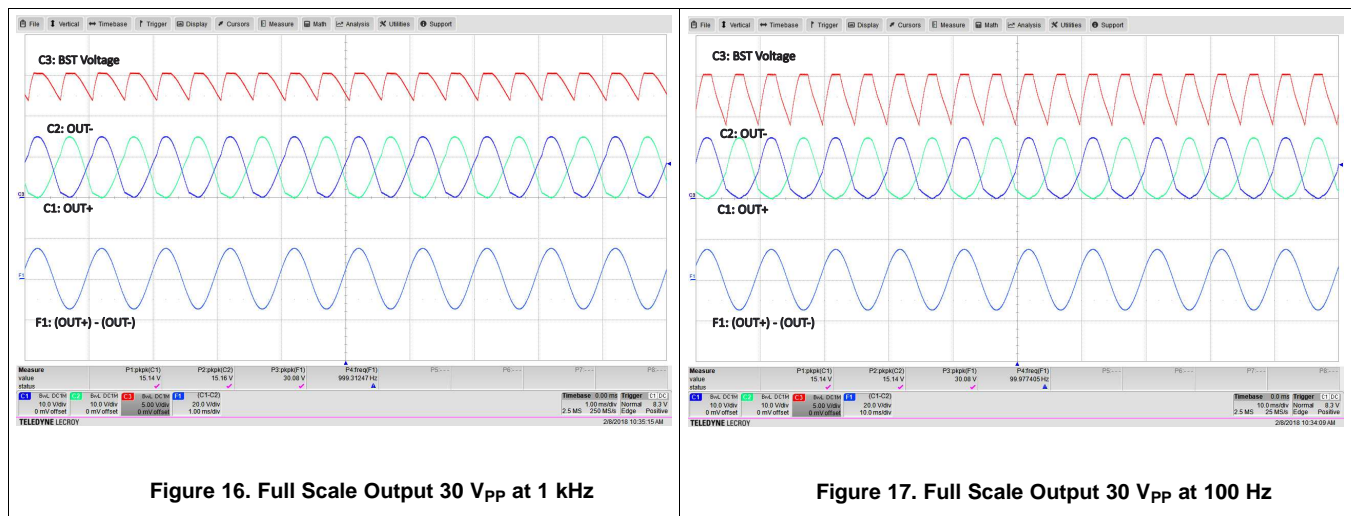
| MANUFACTURER | PART#        | INDUCTANCE/ISAT                 |
|--------------|--------------|---------------------------------|
| Taiyo Yuden  | BRL3225T4R7M | 4.7 $\mu\text{H}/1.1 \text{ A}$ |
| Coilcraft    | LP3015       | 4.7 $\mu\text{H}/1.1 \text{ A}$ |

(1) See [Development Support](#)

##### 14.2.2.1.2 Diode Selection

Use a Schottkey diode as shown in the *Functional Block Diagram*. A 20 V diode such as the NSR0520V2T1G from On Semiconductor is recommended. The NSR0520V2T1G is designed to handle a maximum average current of 500 mA.

#### 14.2.2.2 Application Curves



## 15 Power Supply Recommendations

The LM48580 device is designed to operate with a power supply between 2.5 V and 5.5 V. Proper power supply bypassing is critical for low noise performance and high PSRR. Place the supply bypass capacitors as close to the device as possible. Place a 1- $\mu\text{F}$  ceramic capacitor from VDD to GND. Additional bulk capacitance may be added as required.

## 16 Layout

### 16.1 Layout Guidelines

- Minimize trace impedance of the power, ground and all output traces for optimum performance.
- Voltage loss due to trace resistance between the LM48580 and the load results in decreased output power and efficiency.
- Trace resistance between the power supply and ground has the same effect as a poorly regulated supply, increased ripple and reduced peak output power.
- Use wide traces for power supply inputs and amplifier outputs to minimize losses due to trace resistance, as well as route heat away from the device.
- Proper grounding improves audio performance, minimizes crosstalk between channels and prevents switching noise from interfering with the audio signal.
- Use of power and ground planes is recommended.

Place all digital components and route digital signal traces as far as possible from analog components and traces. Do not run digital and analog traces in parallel on the same PCB layer. If digital and analog signal lines must cross either over or under each other, ensure that they cross in a perpendicular fashion.

### 16.2 Layout Example

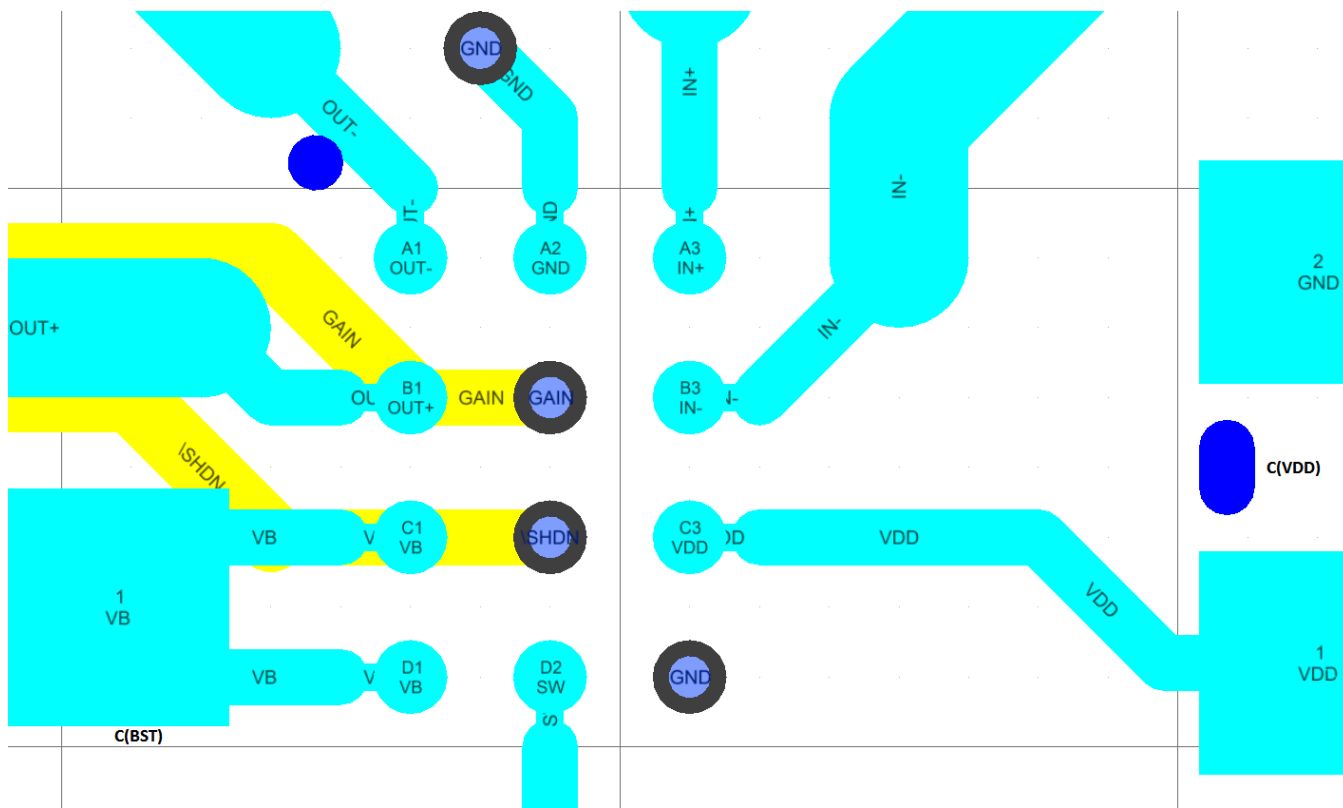


Figure 18. Example Layout

## 17 Device and Documentation Support

### 17.1 Device Support

#### 17.1.1 Development Support

##### 17.1.1.1 *Third-Party Products Disclaimer*

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### 17.2 Receiving Notification of Documentation Updates

To receive notification of documentation updates, navigate to the device product folder on ti.com. In the upper right corner, click on *Alert me* to register and receive a weekly digest of any product information that has changed. For change details, review the revision history included in any revised document.

### 17.3 Community Resources

The following links connect to TI community resources. Linked contents are provided "AS IS" by the respective contributors. They do not constitute TI specifications and do not necessarily reflect TI's views; see TI's [Terms of Use](#).

**TI E2E™ Online Community** *TI's Engineer-to-Engineer (E2E) Community*. Created to foster collaboration among engineers. At e2e.ti.com, you can ask questions, share knowledge, explore ideas and help solve problems with fellow engineers.

**Design Support** *TI's Design Support* Quickly find helpful E2E forums along with design support tools and contact information for technical support.

### 17.4 Trademarks

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### 17.5 Electrostatic Discharge Caution



This integrated circuit can be damaged by ESD. Texas Instruments recommends that all integrated circuits be handled with appropriate precautions. Failure to observe proper handling and installation procedures can cause damage.

ESD damage can range from subtle performance degradation to complete device failure. Precision integrated circuits may be more susceptible to damage because very small parametric changes could cause the device not to meet its published specifications.

### 17.6 Glossary

[SLYZ022](#) — *TI Glossary*.

This glossary lists and explains terms, acronyms, and definitions.

## 18 Mechanical, Packaging, and Orderable Information

The following pages include mechanical, packaging, and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser-based versions of this data sheet, refer to the left-hand navigation.

**PACKAGING INFORMATION**

| Orderable Device | Status<br>(1) | Package Type | Package Drawing | Pins | Package Qty | Eco Plan<br>(2) | Lead finish/<br>Ball material<br>(6) | MSL Peak Temp<br>(3) | Op Temp (°C) | Device Marking<br>(4/5) | Samples                 |
|------------------|---------------|--------------|-----------------|------|-------------|-----------------|--------------------------------------|----------------------|--------------|-------------------------|-------------------------|
| LM48580TL/NOPB   | ACTIVE        | DSBGA        | YZR             | 12   | 250         | RoHS & Green    | SNAGCU                               | Level-1-260C-UNLIM   | -40 to 85    | GM3                     | <a href="#">Samples</a> |
| LM48580TLX/NOPB  | ACTIVE        | DSBGA        | YZR             | 12   | 3000        | RoHS & Green    | SNAGCU                               | Level-1-260C-UNLIM   | -40 to 85    | GM3                     | <a href="#">Samples</a> |

(1) The marketing status values are defined as follows:

**ACTIVE:** Product device recommended for new designs.

**LIFEBUY:** TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

**NRND:** Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

**PREVIEW:** Device has been announced but is not in production. Samples may or may not be available.

**OBSOLETE:** TI has discontinued the production of the device.

(2) **RoHS:** TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".

**RoHS Exempt:** TI defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.

**Green:** TI defines "Green" to mean the content of Chlorine (Cl) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <=1000ppm threshold. Antimony trioxide based flame retardants must also meet the <=1000ppm threshold requirement.

(3) MSL, Peak Temp. - The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

(4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.

(5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.

(6) Lead finish/Ball material - Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

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**TAPE AND REEL INFORMATION**

**QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE**


\*All dimensions are nominal

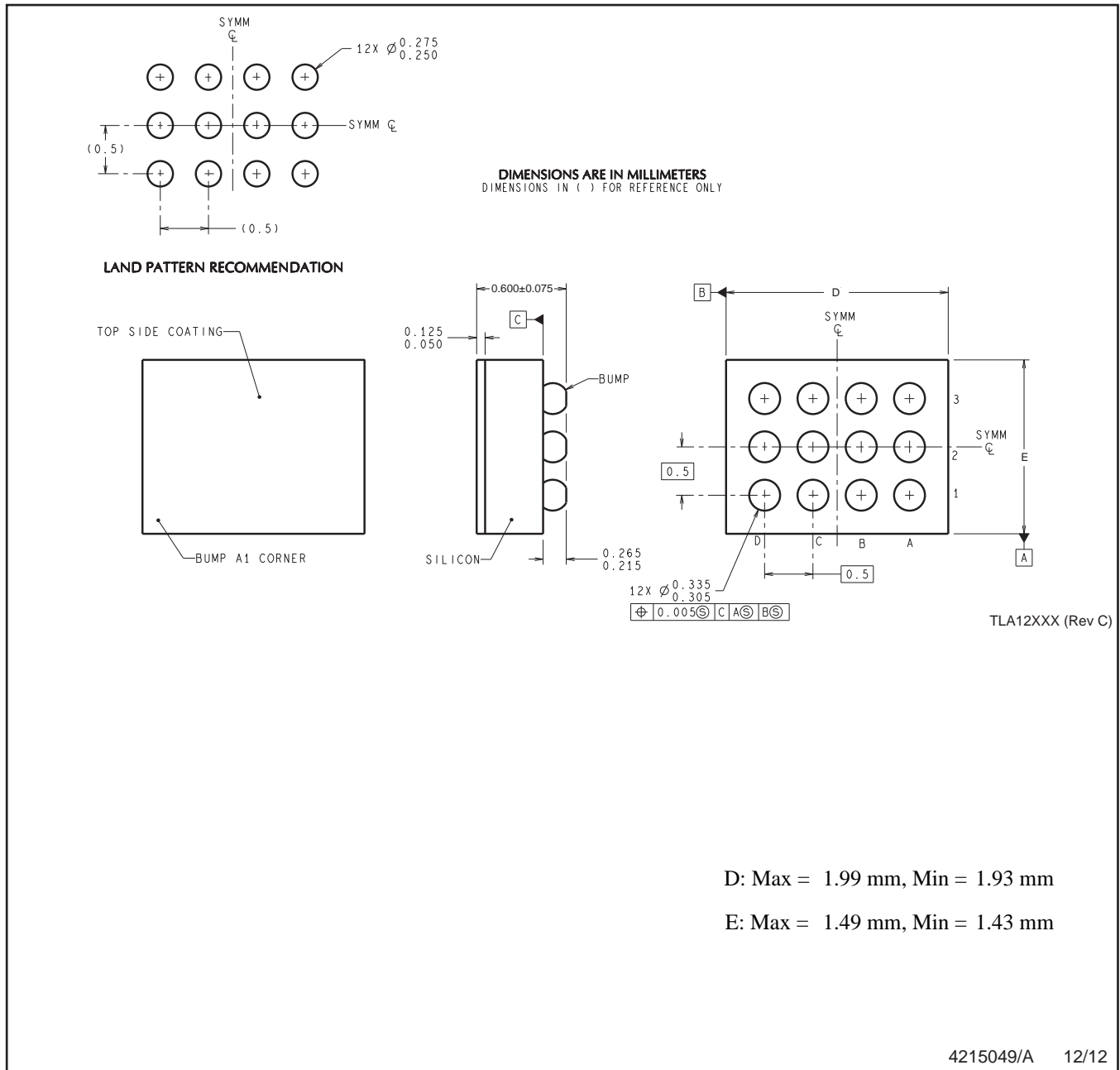
| Device          | Package Type | Package Drawing | Pins | SPQ  | Reel Diameter (mm) | Reel Width W1 (mm) | A0 (mm) | B0 (mm) | K0 (mm) | P1 (mm) | W (mm) | Pin1 Quadrant |
|-----------------|--------------|-----------------|------|------|--------------------|--------------------|---------|---------|---------|---------|--------|---------------|
| LM48580TL/NOPB  | DSBGA        | YZR             | 12   | 250  | 178.0              | 8.4                | 1.68    | 2.13    | 0.76    | 4.0     | 8.0    | Q1            |
| LM48580TLX/NOPB | DSBGA        | YZR             | 12   | 3000 | 178.0              | 8.4                | 1.68    | 2.13    | 0.76    | 4.0     | 8.0    | Q1            |

**TAPE AND REEL BOX DIMENSIONS**


\*All dimensions are nominal

| Device          | Package Type | Package Drawing | Pins | SPQ  | Length (mm) | Width (mm) | Height (mm) |
|-----------------|--------------|-----------------|------|------|-------------|------------|-------------|
| LM48580TL/NOPB  | DSBGA        | YZR             | 12   | 250  | 208.0       | 191.0      | 35.0        |
| LM48580TLX/NOPB | DSBGA        | YZR             | 12   | 3000 | 208.0       | 191.0      | 35.0        |

YZR0012



D: Max = 1.99 mm, Min = 1.93 mm

E: Max = 1.49 mm, Min = 1.43 mm

4215049/A 12/12

NOTES: A. All linear dimensions are in millimeters. Dimensioning and tolerancing per ASME Y14.5M-1994.  
B. This drawing is subject to change without notice.

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